

Device Modeling Report

COMPONENTS:
DIODE/ GENERAL PURPOSE RECTIFIER/ PROFESSIONAL
PART NUMBER: 1N5408
MANUFACTURER: FAIRCHILD SEMICONDUCTOR



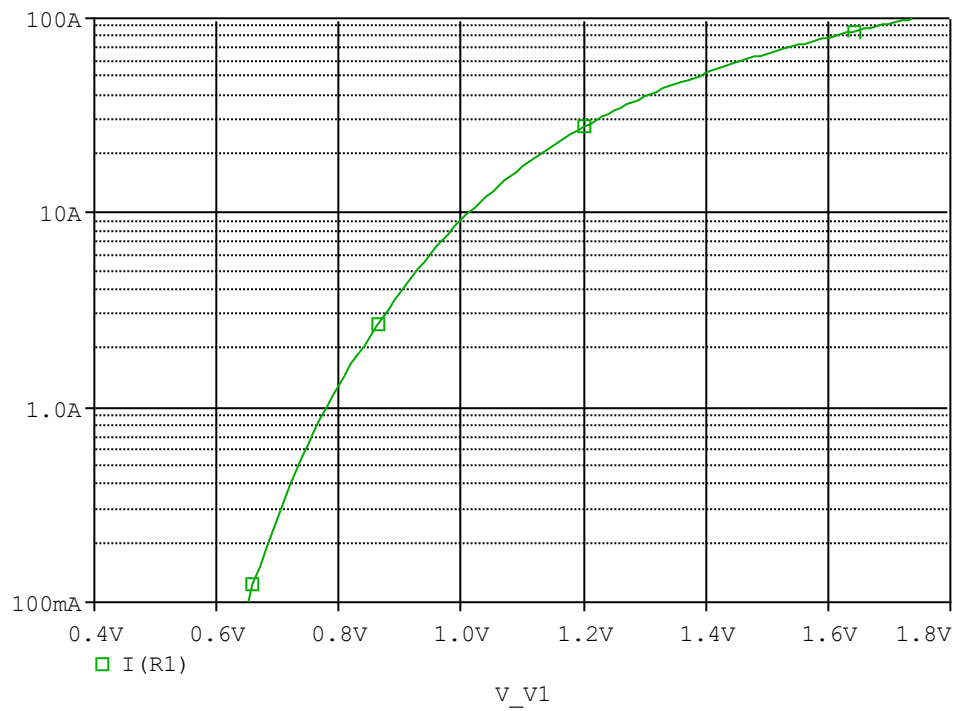
Bee Technologies Inc.

DIODE MODEL PARAMETERS

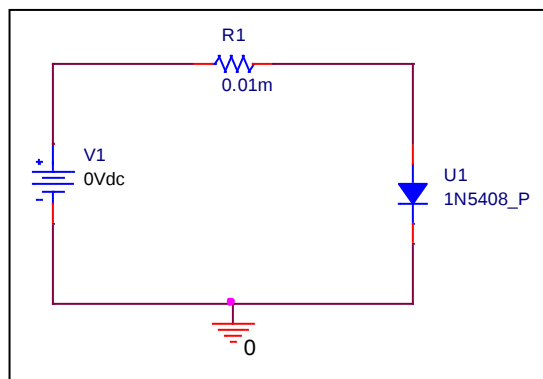
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristics

Circuit Simulation Result

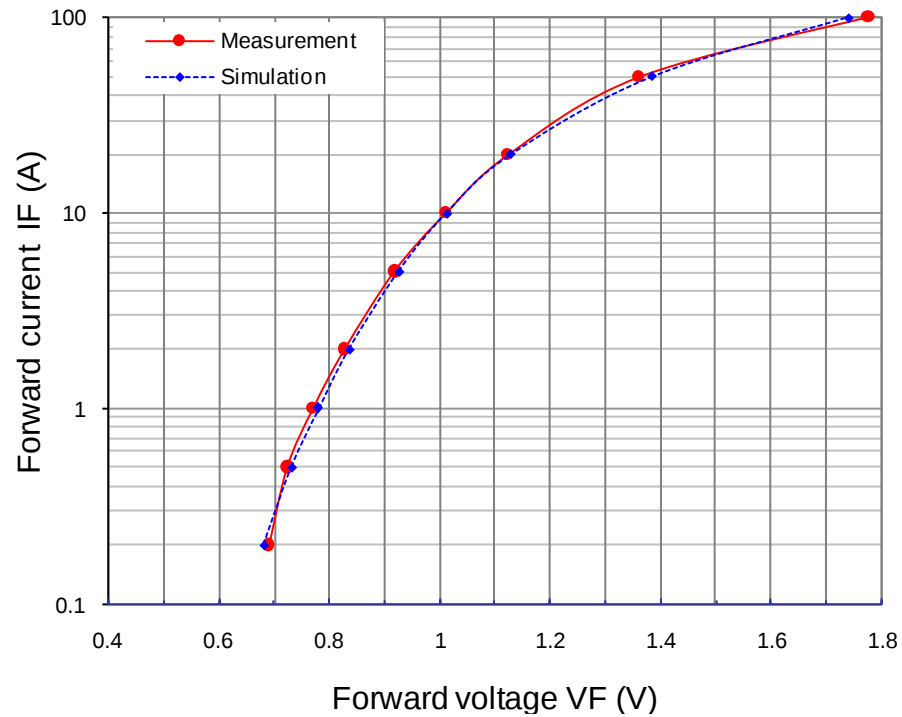


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

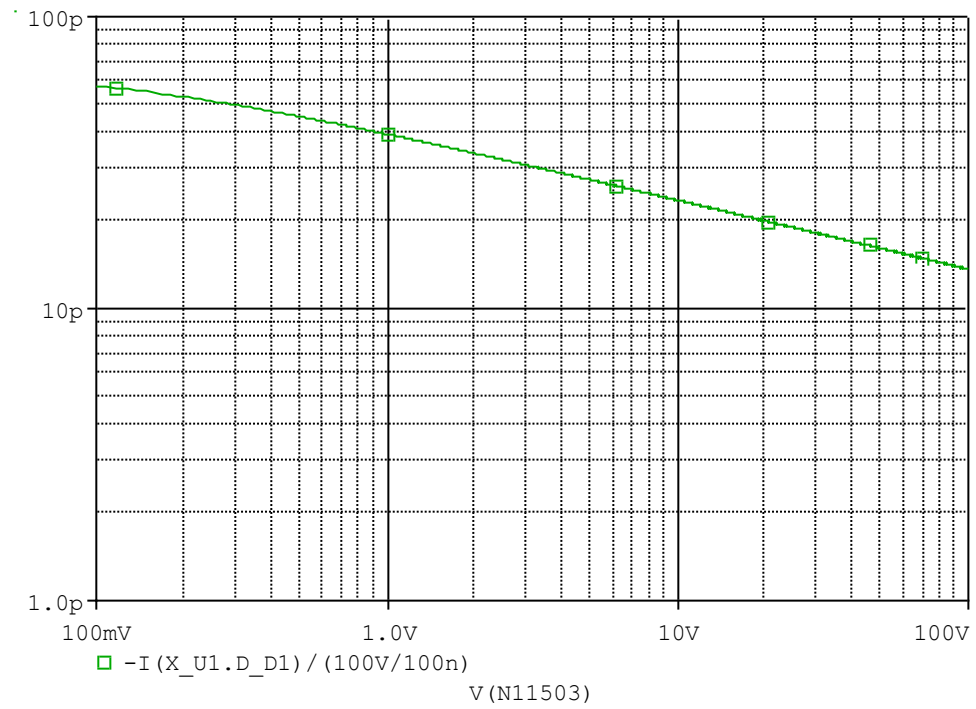


Simulation Result

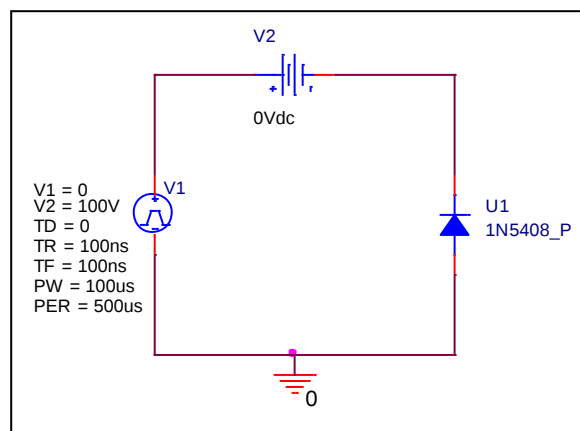
IF (A)	VF (V)		%Error
	Measurement	Simulation	
0.2	0.690	0.682	-1.16
0.5	0.725	0.733	1.08
1	0.770	0.780	1.29
2	0.828	0.836	1.01
5	0.920	0.927	0.71
10	1.010	1.012	0.23
20	1.123	1.128	0.48
50	1.360	1.383	1.68
100	1.775	1.739	-2.01

Capacitance Characteristics

Circuit Simulation Result

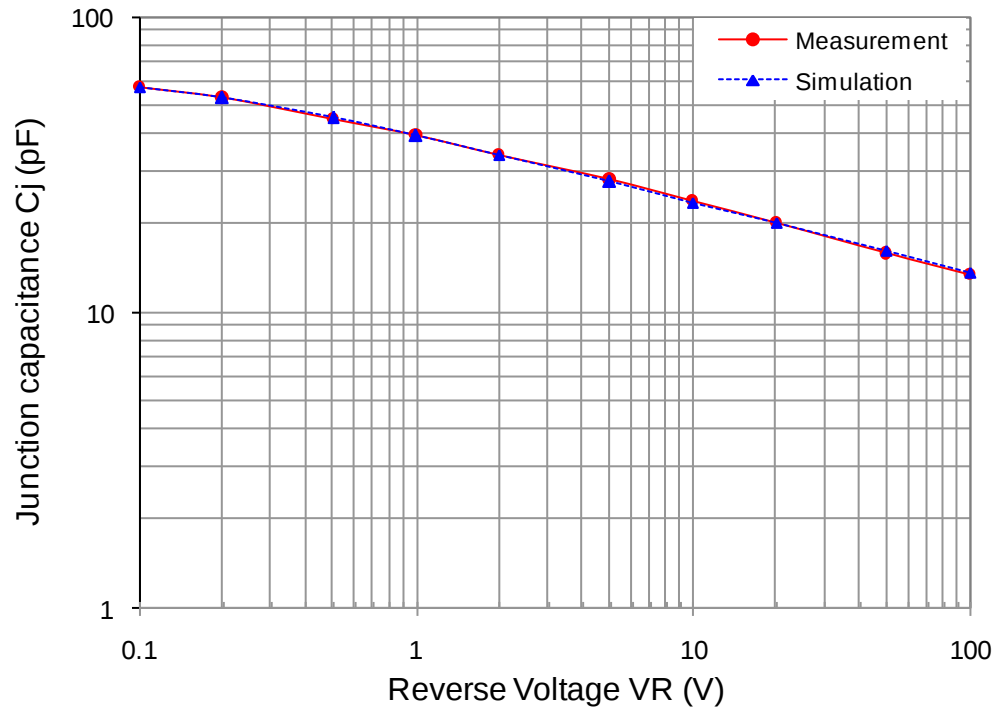


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

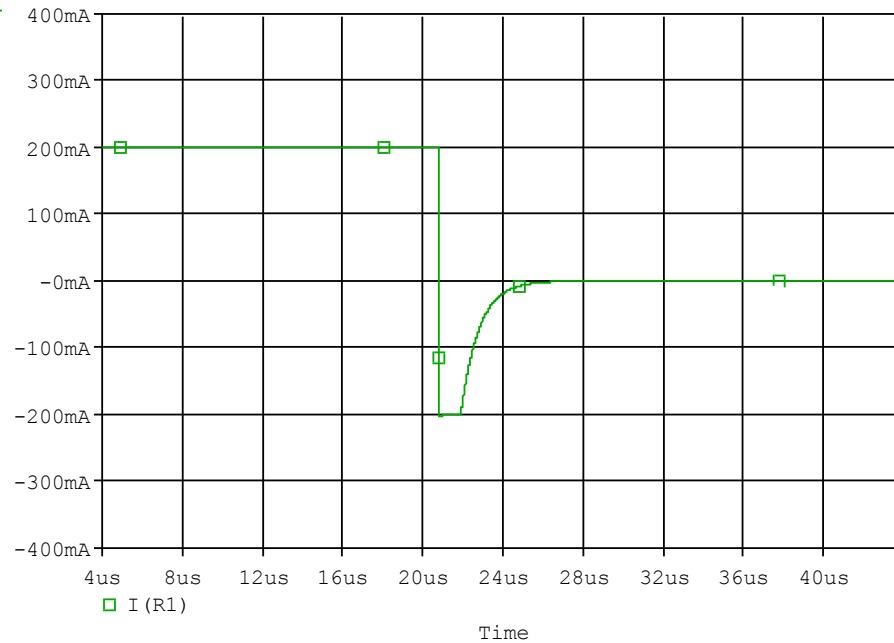


Simulation Result

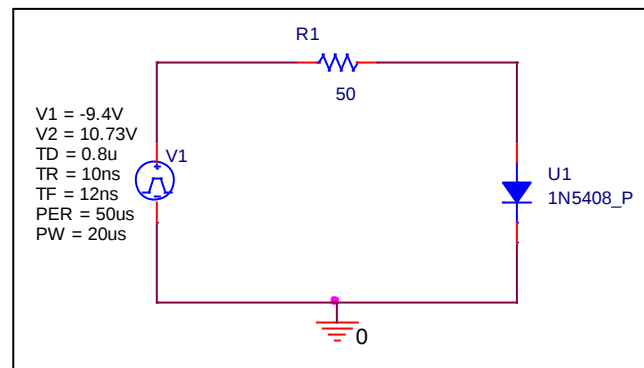
VR (V)	Cj (pF)		%Error
	Measurement	Simulation	
0.1	58.000	57.950	-0.09
0.2	53.000	53.082	0.15
0.5	45.000	45.500	1.11
1	39.750	39.555	-0.49
2	34.000	34.046	0.14
5	28.000	27.632	-1.31
10	23.700	23.503	-0.83
20	20.000	19.969	-0.15
50	15.750	16.081	2.10
100	13.400	13.643	1.81

Reverse Recovery Characteristics

Circuit Simulation Result



Evaluation Circuit

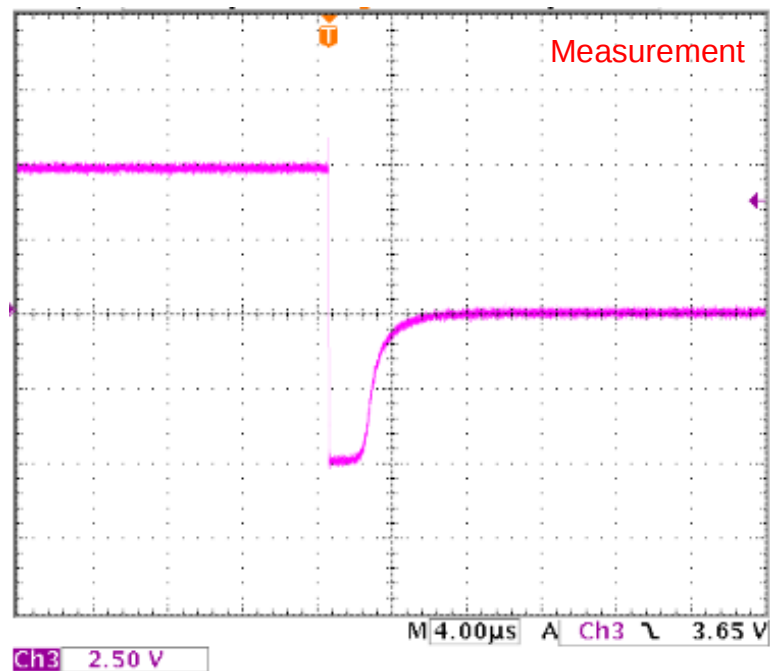


Compare Measurement vs. Simulation

Parameter		Measurement	Simulation	%Error
Trj	μs	1.120	1.114	-0.55
Trb	μs	2.000	2.020	1.00
Trr	μs	3.120	3.134	0.44

Reverse Recovery Characteristics

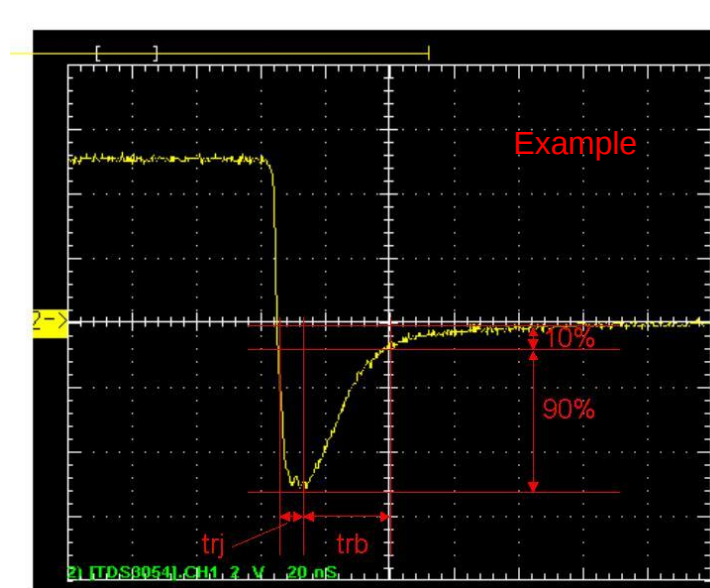
Reference



$T_{rj} = 1.12 \text{ (}\mu\text{s)}$

$T_{rb} = 2.00 \text{ (}\mu\text{s)}$

Conditions: $I_{fwd}=0.2\text{A}$, $I_{rev}=0.2\text{A}$, $R_I=50$



Relation between t_{rj} and t_{rb}